

Monday 4 June

13:50

Pad Detector Characterization & Material Engineering

Session | Location: Vilnius, Lithuania

13:50-14:10

Comparison of neutron damage in thin FZ, MCz and epitaxial silicon detectors

Eckhart Fretwurst

14:10-14:30 Epitaxial silicon detectors irradiated with 23 GeV protons

Speaker

Michael Moll

14:30-14:50 p-type Silicon irradiated with 24 GeV/c protons

Speaker

Vlado Cindro

14:50-15:10

Space charge sign inversion and electric field reconstruction in 24 GeV proton irradiated MCZ Si p+/n(TD)/n+ detectors processed via thermal donor introduction

Speaker

Jaakko Härkönen

15:10-15:30 Update on bias dependent damage in different silicon material

Speaker

Gregor Kramberger

15:30-16:00 Coffee Break

16:00-16:30

Discussion Session (Pad Detector Characterization & Material Engineering)

Speakers

Eckhart Fretwurst, Gregor Kramberger

18:40